



**THE DATASHEET OF
ACST4-7SB-TR**





ACST4 Series

ASD™ AC Switch Family

AC POWER SWITCH

MAIN APPLICATIONS

- AC static switching in appliance control systems
- Drive of low power high inductive or resistive loads like
 - spray pump in dishwashers
 - fan in air-conditioners

FEATURES

- Blocking voltage : $V_{DRM} / V_{RRM} = +/-700V$
- Avalanche controlled : $V_{CL\ typ} = 1100 V$
- Nominal conducting current : $I_{T(RMS)} = 4A$
- High surge current capability: 30A for 20ms full wave
- Gate triggering current : $I_{GT} < 10\ mA$ or 25mA
- Switch integrated driver
- High noise immunity : static $dV/dt > 500V/\mu s$

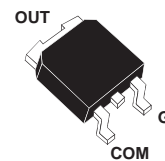
BENEFITS

- Enables equipment to meet IEC 61000-4-5
- High off-state reliability with planar technology
- No external overvoltage protection needed
- Reduces the power component factor
- Interfaces directly with the microcontroller
- Direct interface with the microcontroller for the ACST4-7S ($I_{GT} < 10mA$)

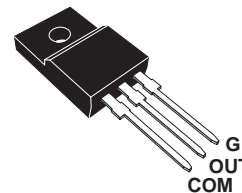
DESCRIPTION

The ACST4 belongs to the AC power switch family built around the ASD™ technology. This high performance device is adapted to home appliances or industrial systems and drives loads up to 4 A.

The ACS™ switch embeds a Triac structure with a high voltage clamping device to absorb the inductive turn-off energy and withstand line transients such as those described in the IEC61000-4-5 standards.

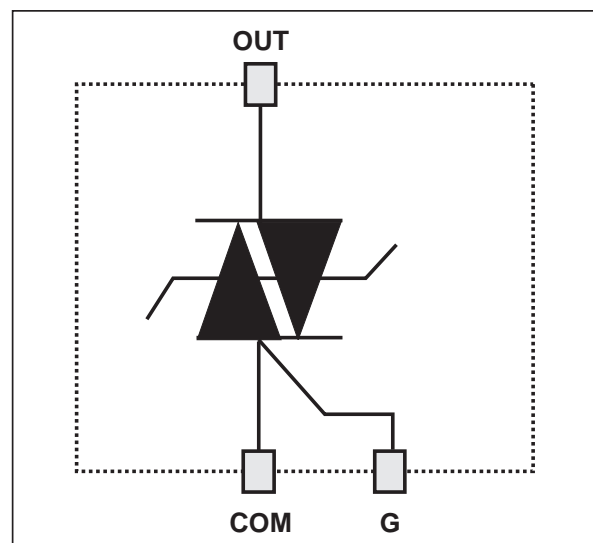


DPAK
ACST4-7SB/CB



TO-220FPAB
ACST4-7SFP/CFP

FUNCTIONAL DIAGRAM



ACST4 Series

ABSOLUTE RATINGS (limiting values)

For either positive or negative polarity of pin OUT voltage in respect to pin COM voltage

| Symbol | Parameter | | Value | Unit |
|---------------------|--|-----------------------|------------------------------|---------------------|
| V_{DRM} / V_{RRM} | Repetitive peak off-state voltage | | $T_j = -10\text{ °C}$ 700 | V |
| $I_{T(RMS)}$ | RMS on-state current full cycle sine wave 50 to 60 Hz | DPAK | $T_c = 110\text{ °C}$ 4 | A |
| | | TO-220FPAB | $T_c = 100\text{ °C}$ | |
| I_{TSM} | Non repetitive surge peak on-state current T_j initial = 25°C, full cycle sine wave | $F = 50\text{ Hz}$ | 30 | A |
| | | $F = 60\text{ Hz}$ | 33 | A |
| I^2t | Fusing capability | | $t_p = 10\text{ms}$ | A ² s |
| di/dt | Repetitive on-state current critical rate of rise $I_G = 10\text{mA}$ ($t_r < 100\text{ns}$) | $T_j = 125\text{ °C}$ | $F = 120\text{ Hz}$ 50 | A/ μs |
| V_{PP} | Non repetitive line peak pulse voltage | | note 1 2 | kV |
| T_{stg} | Storage temperature range | | | - 40 to + 150 °C |
| T_j | Operating junction temperature range | | | - 30 to + 125 °C |
| T_l | Maximum lead soldering temperature during 10s | | | 260 °C |

Note 1: according to test described by IEC61000-4-5 standard & Figure B.

GATE CHARACTERISTICS (maximum values)

| Symbol | Parameter | Value | Unit |
|-------------|---|-------|------|
| $P_{G(AV)}$ | Average gate power dissipation | 0.1 | W |
| P_{GM} | Peak gate power dissipation ($t_p = 20\mu\text{s}$) | 10 | A |
| I_{GM} | Peak gate current ($t_p = 20\mu\text{s}$) | 1 | V |

THERMAL RESISTANCES

| Symbol | Parameter | | Value | Unit |
|---------------|--|-----------------------------|-------|------|
| $R_{th(j-a)}$ | Junction to ambient | $S = 0.5\text{cm}^2$ DPAK | 70 | °C/W |
| | | TO-220FPAB | 60 | °C/W |
| $R_{th(j-l)}$ | Junction to case for full cycle sine wave conduction | DPAK | 2.6 | °C/W |
| | | TO-220FPAB | 4.6 | °C/W |

S = Copper surface under Tab

PARAMETER DESCRIPTION

| Parameter Symbol | Parameter description |
|---------------------|---|
| I_{GT} | Triggering gate current |
| V_{GT} | Triggering gate voltage |
| V_{GD} | Non-triggering gate voltage |
| I_H | Holding current |
| I_L | Latching current |
| V_{TM} | Peak on-state voltage drop |
| V_{TO} | On state threshold voltage |
| R_d | On state dynamic resistance |
| I_{DRM} / I_{RRM} | Maximum forward or reverse leakage current |
| dV/dt | Critical rate of rise of off-state voltage |
| $(dV/dt)_c$ | Critical rate of rise of commutating off-state voltage |
| $(dI/dt)_c$ | Critical rate of decrease of commutating on-state current |
| V_{CL} | Clamping voltage |
| I_{CL} | Clamping current |

ELECTRICAL CHARACTERISTICS

For either positive or negative polarity of pin OUT voltage in respect to pin COM voltage.

| Symbol | Test Conditions | | | | ACST4-7S | ACST4-7C | Unit |
|---------------------|--------------------------------------|-----------------|-------------------|-----|----------|----------|------------|
| I_{GT} | $V_{OUT}=12V$ (DC) $R_L=33\Omega$ | QI - QII - QIII | $T_j=25^\circ C$ | MAX | 10 | 25 | mA |
| V_{GT} | $V_{OUT}=12V$ (DC) $R_L=33\Omega$ | QI - QII - QIII | $T_j=25^\circ C$ | MAX | 1 | 1.1 | V |
| V_{GD} | $V_{OUT}=V_{DRM}$ $R_L=3.3k\Omega$ | | $T_j=125^\circ C$ | MIN | 0.2 | | V |
| I_H | $I_{OUT}=100mA$ gate open | | $T_j=25^\circ C$ | MAX | 20 | 35 | mA |
| I_L | $I_G=2 \times I_{GTmax}$ | | $T_j=25^\circ C$ | MAX | 40 | 60 | mA |
| V_{TM} | $I_{OUT}=5.6A$ $t_p=380\mu s$ | | $T_j=25^\circ C$ | MAX | 1.5 | | V |
| V_{TO} | | | $T_j=125^\circ C$ | MAX | 0.90 | | V |
| R_d | | | $T_j=125^\circ C$ | MAX | 100 | | m Ω |
| I_{DRM} / I_{RRM} | $V_{OUT}=700V$ | | $T_j=25^\circ C$ | MAX | 10 | | μA |
| | | | $T_j=125^\circ C$ | MAX | 500 | | |
| dV/dt | $V_{OUT}=460V$ gate open | | $T_j=110^\circ C$ | MIN | 200 | 500 | V/ μs |
| $(dI/dt)_c$ | $(dV/dt)_c=15V/\mu s$ | | $T_j=125^\circ C$ | MIN | 2.0 | 2.5 | A/ms |
| V_{CL} | $I_{CL}=1mA$ $t_p=1ms$ | | $T_j=25^\circ C$ | TYP | 1100 | | V |

Fig. B: Overvoltage ruggedness test circuit for resistive and inductive loads according to IEC61000-4-5 standards.
 $R = 150\Omega$, $L = 10\mu\text{H}$, $V_{PP} = 2\text{kV}$.

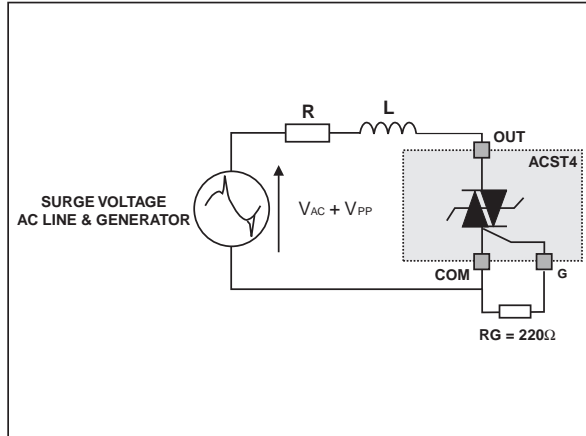


Fig. C: Current and Voltage of the ACST4 during IEC61000-4-5 standard test with R, L & V_{PP} .

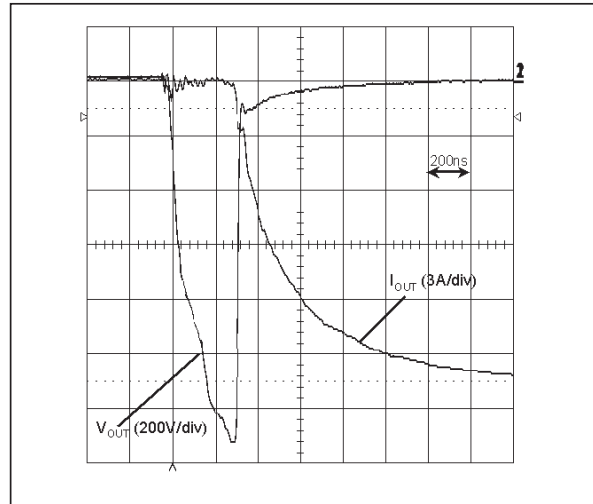


Fig. 1: Maximum power dissipation versus RMS on-state current.

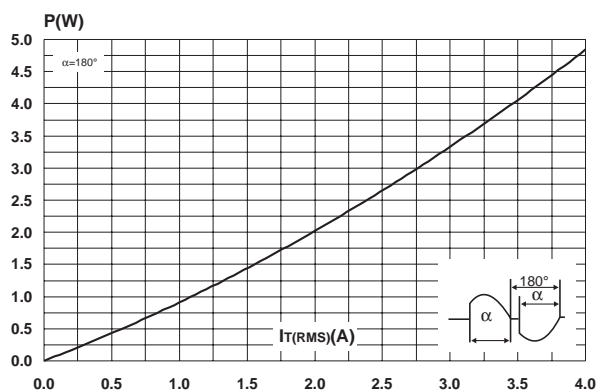


Fig. 2-1: RMS on-state current versus case temperature.

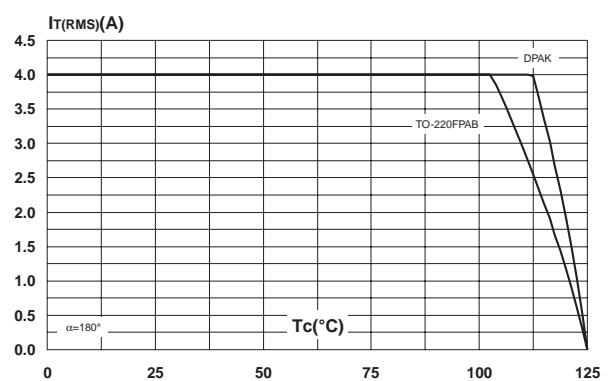


Fig. 2-2: RMS on-state current versus ambient temperature.

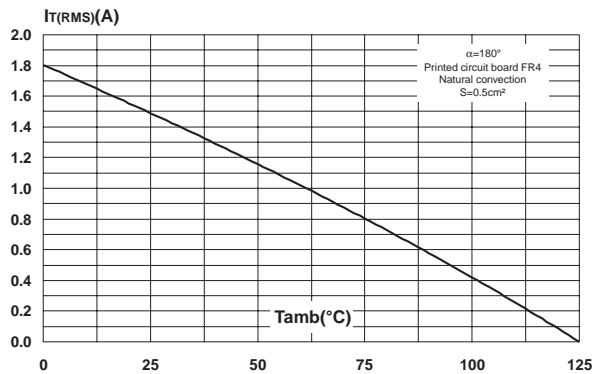


Fig. 3: Relative variation of thermal impedance versus pulse duration.

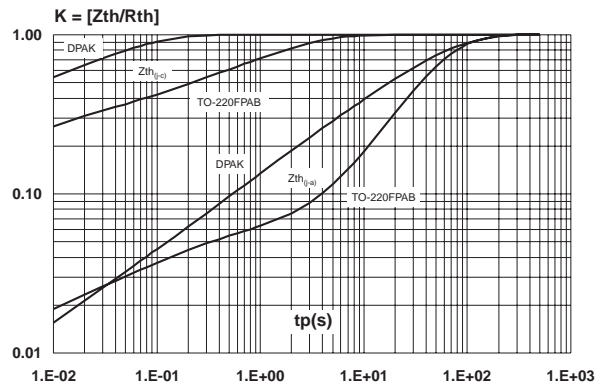


Fig. 4: Relative variation of gate trigger current, holding current and latching versus junction temperature (typical values).

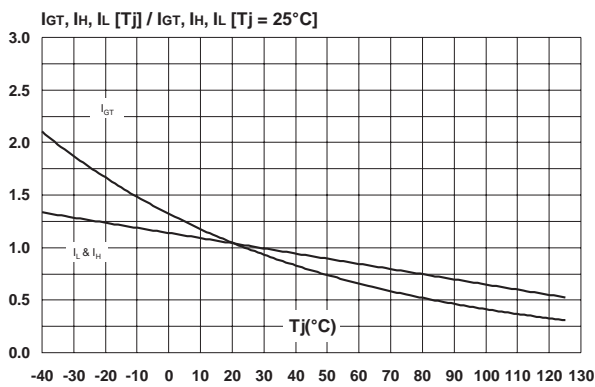


Fig. 5: Relative variation of static dV/dt versus junction temperature.

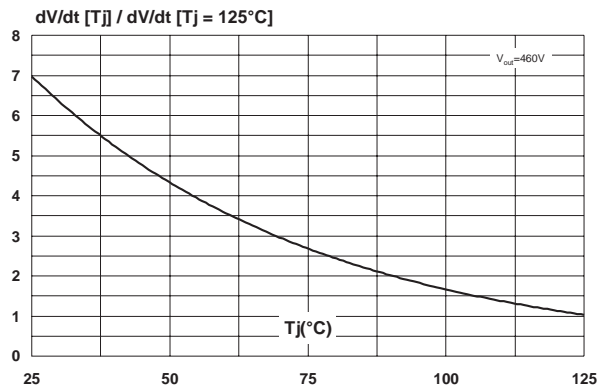


Fig. 6-1: Relative variation of critical rate of decrease of main current versus reapplied dV/dt (typical values).

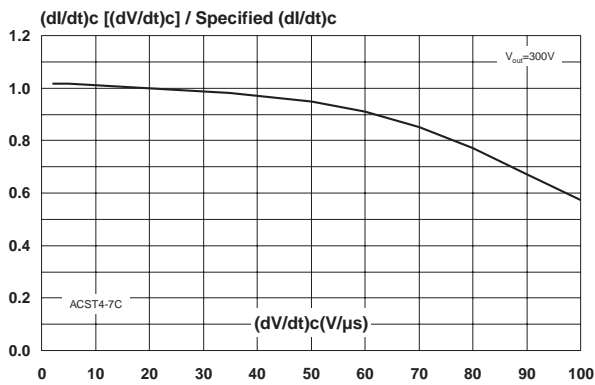


Fig. 6-2: Relative variation of critical rate of decrease of main current versus reapplied dV/dt (typical values).

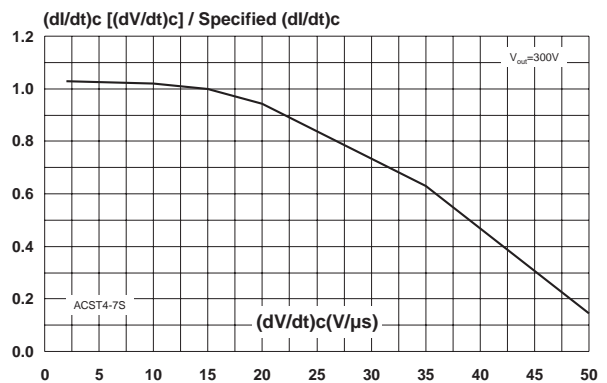


Fig. 7: Relative variation of critical rate of decrease of main current versus junction temperature.

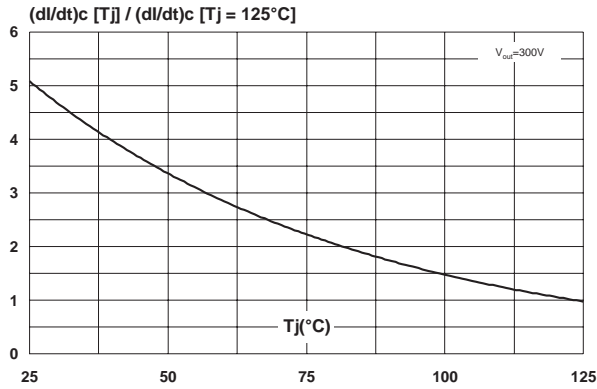


Fig. 8: Surge peak on-state current versus number of cycles.

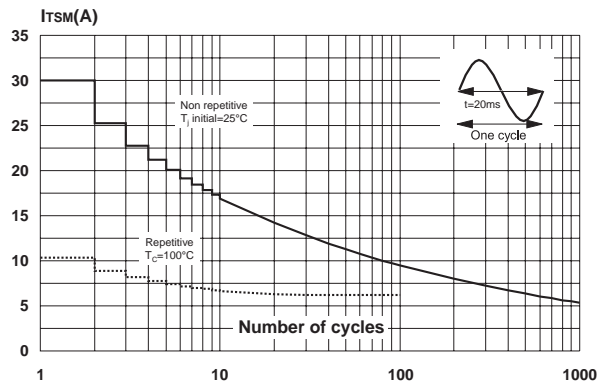


Fig. 9: Non repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t .

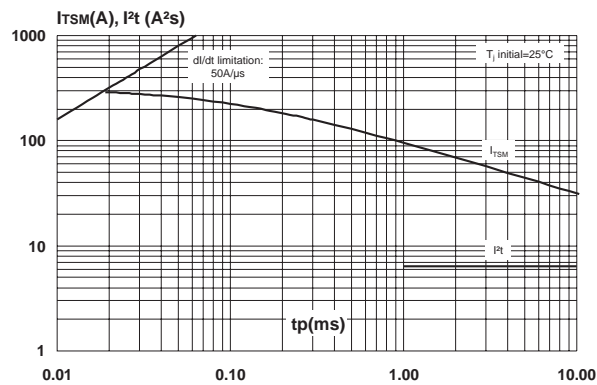


Fig. 10: On-state characteristics (maximum values).

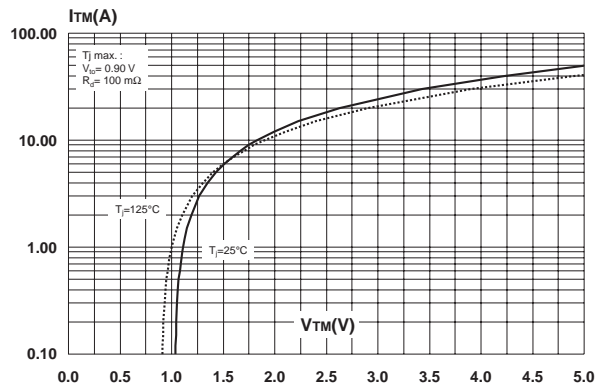
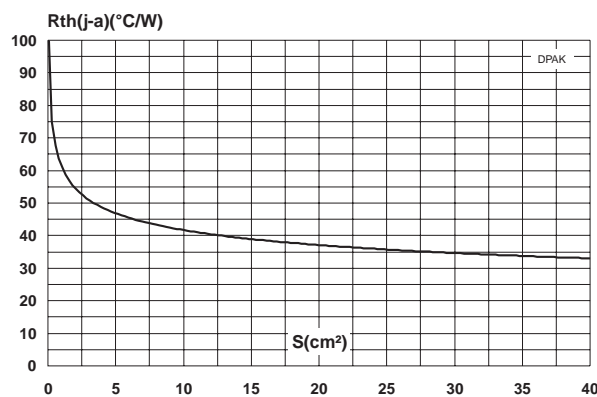
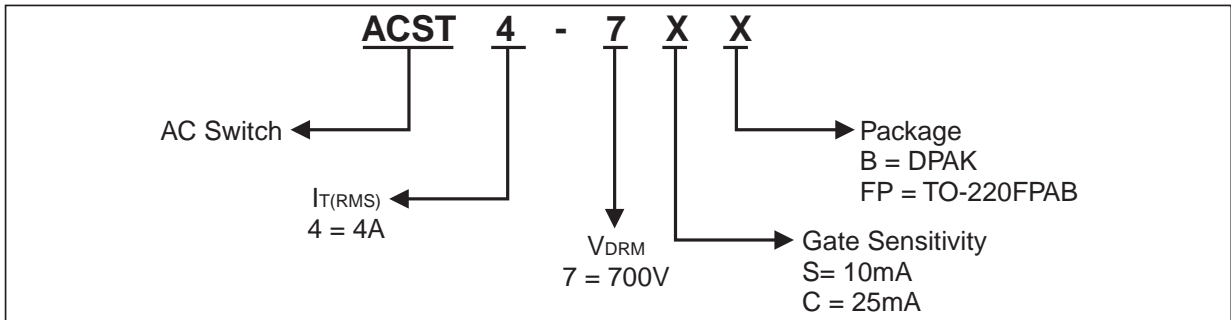


Fig. 11: Thermal resistance junction to ambient versus copper surface under tab (printed circuit board FR4, copper thickness: $35\mu\text{m}$)

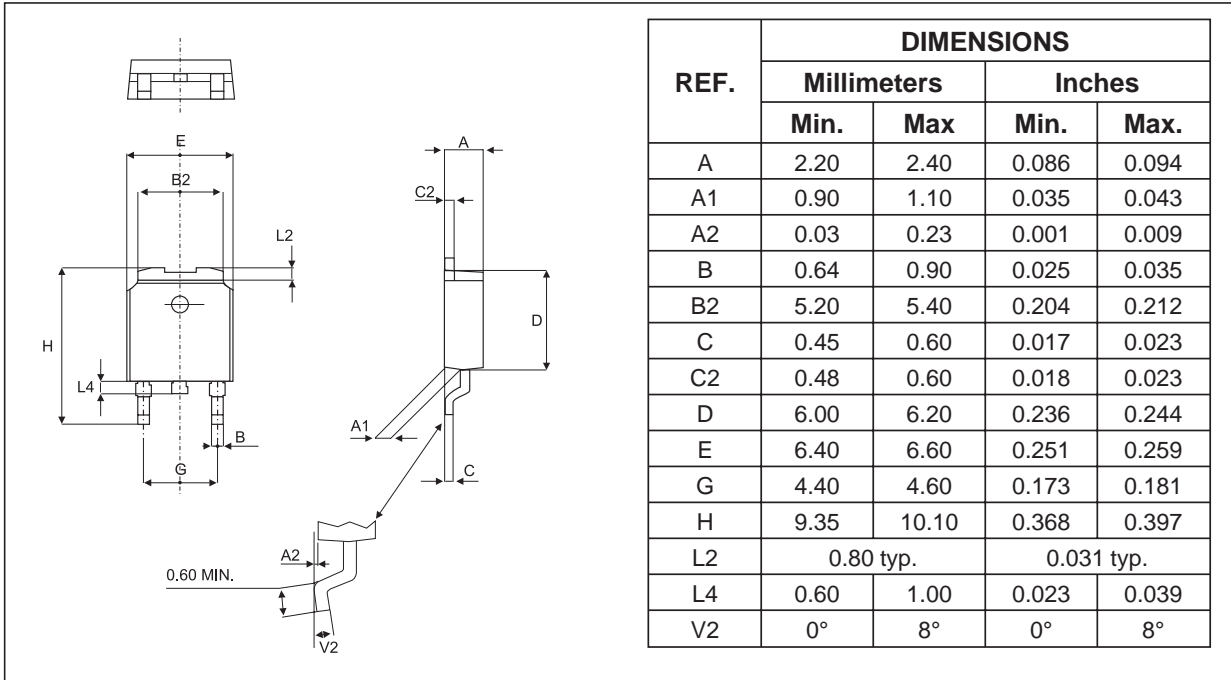


ACST4 Series

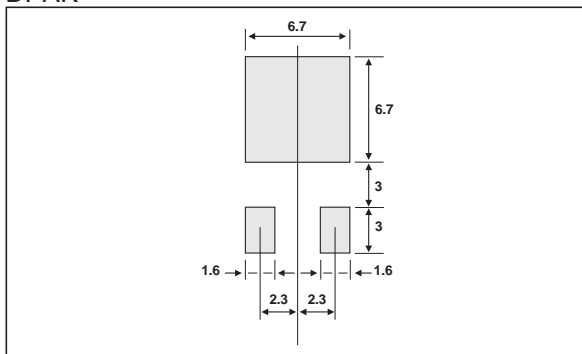
ORDERING INFORMATION



PACKAGE OUTLINE MECHANICAL DATA DPAK



FOOT PRINT DPAK



PACKAGE OUTLINE MECHANICAL DATA
TO-220FPAB

| REF. | DIMENSIONS | | | |
|------|-------------|------|-----------|-------|
| | Millimeters | | Inches | |
| | Min. | Max. | Min. | Max. |
| A | 4.4 | 4.6 | 0.173 | 0.181 |
| B | 2.5 | 2.7 | 0.098 | 0.106 |
| D | 2.5 | 2.75 | 0.098 | 0.108 |
| E | 0.45 | 0.70 | 0.018 | 0.027 |
| F | 0.75 | 1 | 0.030 | 0.039 |
| F1 | 1.15 | 1.70 | 0.045 | 0.067 |
| F2 | 1.15 | 1.70 | 0.045 | 0.067 |
| G | 4.95 | 5.20 | 0.195 | 0.205 |
| G1 | 2.4 | 2.7 | 0.094 | 0.106 |
| H | 10 | 10.4 | 0.393 | 0.409 |
| L2 | 16 Typ. | | 0.63 Typ. | |
| L3 | 28.6 | 30.6 | 1.126 | 1.205 |
| L4 | 9.8 | 10.6 | 0.386 | 0.417 |
| L5 | 2.9 | 3.6 | 0.114 | 0.142 |
| L6 | 15.9 | 16.4 | 0.626 | 0.646 |
| L7 | 9.00 | 9.30 | 0.354 | 0.366 |

OTHER INFORMATION

| Ordering type | Marking | Package | Weight | Base qty | Delivery mode |
|---------------|---------|------------|--------|----------|---------------|
| ACST4-7SB | ACST47S | DPAK | 0.3 g | 75 | Tube |
| ACST4-7SB-TR | ACST47S | DPAK | 0.3 g | 2500 | Tape & reel |
| ACST4-7SFP | ACST47S | TO-220FPAB | 2.4 g | 50 | Tube |
| ACST4-7CB | ACST47C | DPAK | 0.3 g | 75 | Tube |
| ACST4-7CB-TR | ACST47C | DPAK | 0.3 g | 2500 | Tape & reel |
| ACST4-7CFP | ACST47C | TO-220FPAB | 2.4 g | 50 | Tube |

- Epoxy meets UL94,V0

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